BAS70LT1G

Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Low Forward Voltage
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 150°C unless otherwise noted)

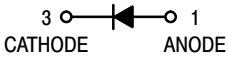
Rating	Symbol	Value	Unit
Forward Current	I_F	70	mA
Non−Repetitive Peak Forward Surge Current (t ≤ 1.0 s)	I_{FSM}	100	mA
Reverse Voltage	V_R	70	V
Forward Power Dissipation @ T_A = 25°C Derate above 25°C	P_F	 225 1.8	 mW mW/°C
Operating Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

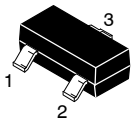
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ON Semiconductor®

http://onsemi.com

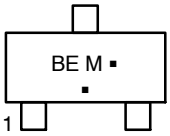
70 VOLTS SCHOTTKY BARRIER DIODES





SOT−23
CASE 318
STYLE 8

MARKING DIAGRAM



BE = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BAS70LT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage – (I_R = 10 μA)	$V_{(BR)R}$	70	–	V
Total Capacitance – (V_R = 0 V, f = 1.0 MHz)	C_T	–	2.0	pF
Reverse Leakage (V_R = 50 V) (V_R = 70 V)	I_R	 – –	 0.1 10	μA
Forward Voltage – (I_F = 1.0 mA)	V_F	–	410	mV
Forward Voltage – (I_F = 10 mA)	V_F	–	750	mV
Forward Voltage – (I_F = 15 mA)	V_F	–	1.0	V

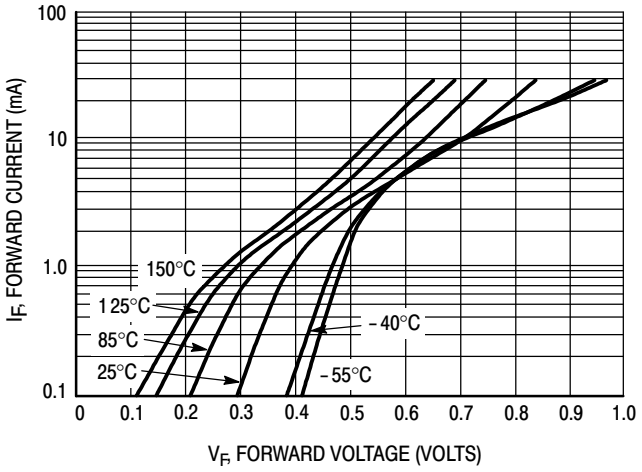


Figure 1. Typical Forward Voltage

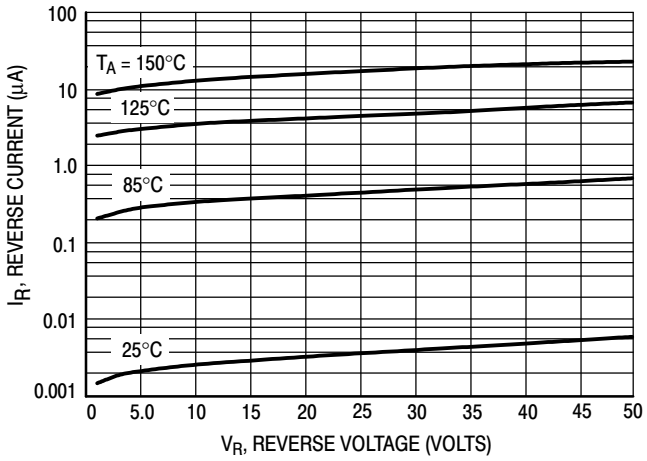


Figure 2. Reverse Current versus Reverse Voltage

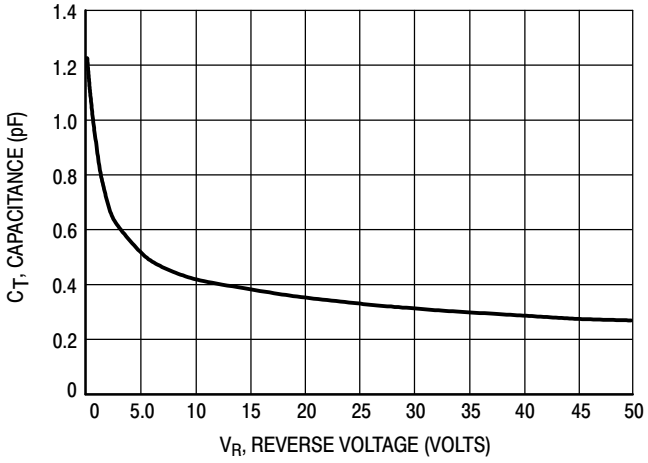
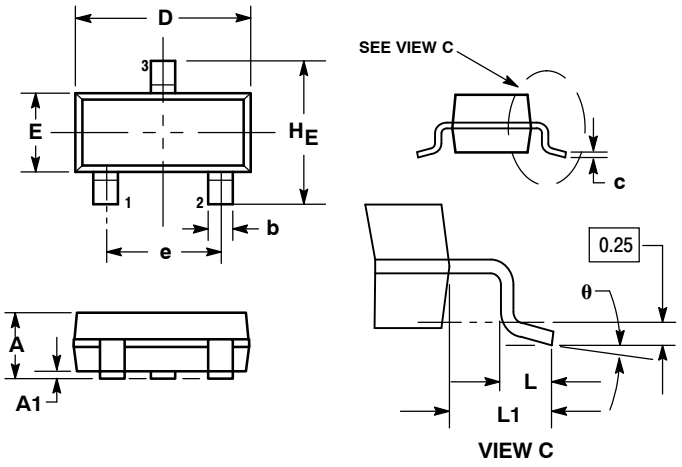


Figure 3. Typical Capacitance

BAS70LT1G

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AN

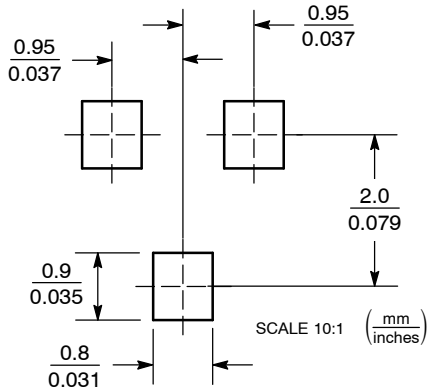


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01 THRU −07 AND −09 OBSOLETE, NEW STANDARD 318−08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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Japan Customer Focus Center
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ON Semiconductor Website: **www.onsemi.com**

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For additional information, please contact your local Sales Representative

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